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Substitute for form 1449A/B/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(Use as many sheets as necessary)</i>				<b>Complete if Known</b>	
				Application Number	Not Yet Assigned
				Filing Date	Concurrently Herewith
				First Named Inventor	Kristy A. Campbell
				Art Unit	N/A
				Examiner Name	Not Yet Assigned
Sheet	1	of	10	Attorney Docket Number	M4065.0635/P635 A

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
78	AA	6,469,364	10/2002	Kozicki	
	AB	2002/0168820 App.	11/2002	Kozicki	
	AC	2000/0072188 App.	6/2002	Gilton	
	AD	2002/0123169 App.	9/2002	Moore et al.	
	AE	2002/0123248 App.	9/2002	Moore et al.	
	AF	3,622,319	11/1971	Sharp	
	AG	3,743,847	7/1973	Boland	
	AH	4,269,935	5/1981	Masters et al.	
	AI	4,312,938	1/1982	Drexler, et al.	
	AJ	4,316,946	1/1982	Masters, et al.	
	AK	4,320,191	3/1982	Yoshikawa et al.	
	AL	4,405,710	9/1983	Balasubramanyam et al.	
	AM	4,419,421	12/1983	Wichelhaus, et al.	
	AN	4,795,657	1/1989	Formigoni et al.	
	AO	4,847,674	7/1989	Sliwa et al.	
	AP	4,499,557	2/1985	Holmberg et al.	
	AQ	5,177,567	1/1993	Kiersy et al.	
	AR	5,219,788	6/1993	Abernathy et al.	
	AS	5,238,862	8/1993	Blalock et al.	
	AT	5,315,131	5/1994	Kishimoto et al.	
	AU	5,350,484	9/1994	Gardner et al.	
	AV	5,360,981	11/1994	Owen et al.	
	AW	5,512,328	4/1996	Yoshimura et al.	
	AX	5,512,773	4/1996	Wolf et al.	
	AY	5,726,083	3/1998	Takaishi	
	AZ	5,841,150	11/1998	Gonzalez et al.	
	AA1	5,846,889	12/1998	Harbison et al.	
	AB1	5,920,788	7/1999	Reinberg	
	AC1	5,998,066	12/1999	Block et al.	
	AD1	6,077,729	6/2000	Harshfield	
	AE1	6,117,720	9/2000	Harshfield	
	AF1	6,143,604	11/2000	Chiang et al.	
	AG1	6,177,338	1/2001	Liaw et al.	
	AH1	6,236,059	5/2001	Wolstenholme et al.	
	AI1	6,297,170	10/2001	Gabriel et al.	
	AJ1	6,300,684	10/2001	Gonzalez et al.	
	AK1	6,316,784	11/2001	Zahorik et al.	
	AL1	6,329,606	12/2001	Freyman et al.	
	AM1	6,350,679	2/2002	McDaniel et al.	
	AN1	6,376,284	4/2002	Gonzalez et al.	
4	AO1	6,391,688	5/2002	Gonzalez et al.	

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2	AP1	6,414,376	7/2002	Thakur et al.	
	AQ1	6,423,628	7/2002	Li et al.	
	AR1	6,487,106	11/26/2002	Kozicki	
	AS1	5,314,772	5/24/1994	Kozicki	
	AT1	2002/0190350 APP	12/19/2002	Kozicki	
	AU1	2003/0027416 APP	2/6/2003	Moore	
	AW1	2003/0001229 APP	1/2/2003	Moore et al.	
	AV1	2002/0106849 APP	8/8/2002	Moore	
	AX1	2002/0127886 APP	9/12/2002	Moore et al.	
	AY1	2002/0123170 APP	9/5/2002	Moore et al.	
	AZ1	2002/0163828 APP	11/2002	Krieger et al.	
	AA2	6,072,716	6/2000	Jacobson et al.	
	AB2	5,272,359	12/93	Nagasubramanian et al.	
	AC2	4,671,618	6/87	Wu et al.	
	AD2	4,800,526	1/89	Lewis	
	AE2	2003/0035314	02/20/03	Kozicki	
	AF2	2003/0035315	02/20/03	Kozicki	
	AG2	6,473,332	11/2002	Ignatiev, et al.	
	AH2	5,789,277	08/04/1998	Zahorik et al.	
	AI2	6,348,365	02/19/2202	Moore et al.	
	AJ2	5,761,115	06/02/1998	Kozicki et al.	
	AK2	6,084,796	07/04/2000	Kozicki et al.	
	AL2	5,914,893	06/22/1999	Kozicki et al.	
	AM2	5,896,312	04/20/1999	Kozicki et al.	
	AN2	6,388,324	05/14/2002	Kozicki et al.	
	AO2	US 2002/0000666	01/03/2002	Kozicki et al.	
	AP2	5,500,532	03/19/1996	Kozicki et al.	
	AQ2	6,418,049	07/09/2002	Kozicki et al.	
4	AR2	5,751,012	05/12/1998	Wolstenholme et al.	

FOREIGN PATENT DOCUMENTS						
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		Country Code <sup>2</sup> -Number <sup>3</sup> -Kind Code <sup>4</sup> (if known)				
	BA1	JP-56126916		10/1981	Akira et al.	
	BB1	WO 02/21542		03/14/2002	Kozicki et al.	
	BC1	WO 00/48196		08/17/2000	Kozicki et al.	
	BD1	WO 97/48032		12/18/1997	Kozicki et al.	
2	BE1	WO 99/28914		06/10/1999	Kozicki et al.	

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. <sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language translation is attached.

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NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T <sup>2</sup>
W	CA	Axon Technologies Corporation, TECHNOLOGY DESCRIPTION: <i>Programmable Metalization Cell(PMC)</i> , pp. 1-6 (Pre-May 2000).		
	CB	Helbert et al., <i>Intralevel hybrid resist process with submicron capability</i> , SPIE Vol. 333 SUBMICRON LITHOGRAPHY, pp. 24-29 (1982).		
	CC	Hilt, DISSERTATION: <i>Materials characterization of Silver Chalcogenide Programmable Metalization Cells</i> , Arizona State University, pp. Title page-114 (UMI Company, May 1999).		
	CD	Hirose et al., <i>High Speed Memory Behavior and Reliability of an Amorphous As<sub>2</sub>S<sub>3</sub> Film Doped Ag</i> , PHYS. STAT. SOL. (a) 61, pp. 87-90 (1980).		
	CE	Holmquist et al., <i>Reaction and Diffusion in Silver-Arsenic Chalcogenide Glass Systems</i> , 62 J. AMER. CERAM. SOC., No. 3-4, pp. 183-188 (March-April 1979).		
	CF	Huggett et al., <i>Development of silver sensitized germanium selenide photoresist by reactive sputter etching in SF<sub>6</sub></i> , 42 APPL. PHYS. LETT., No. 7, pp. 592-594 (April 1983).		
	CG	Kawaguchi et al., <i>Mechanism of photosurface deposition</i> , 164-166 J. NON-CRYST. SOLIDS, pp. 1231-1234 (1993).		
	CH	Kolobov and Elliott, <i>Photodoping of Amorphous Chalcogenides by Metals</i> , Advances in Physics, Vol. 40, No 5, 625-684 (1991).		
	CI	Kozicki, et al., "Applications of Programmable Resistance Changes in Metal-doped Chalcogenides", Proceedings of the 1999 Symposium on Solid State Ionic Devices, Editors - E.D. Wachsman et al., The Electrochemical Society, Inc., 1 - 12 (1999).		
	CJ	Kozicki, et al., <i>Nanoscale effects in devices based on chalcogenide solid solutions</i> , Superlattices and Microstructures, 27, 485-488 (2000).		
	CK	Kozicki, et al., <i>Nanoscale phase separation in Ag-Ge-Se glasses</i> , Microelectronic Engineering, vol. 63/1-3, 155-159 (2002).		
	CL	M.N. Kozicki and M. Mitkova, <i>Silver incorporation in thin films of selenium rich Ge-Se glasses</i> , Proceedings of the XIX International Congress on Glass, Society for Glass Technology, 226-227 (2001).		
	CM	McHardy et al., <i>The dissolution of metals in amorphous chalcogenides and the effects o electron and ultraviolet radiation</i> , 20 J. PHYS. C.: SOLID STATE PHYS., pp. 4055-4075 (1987)f		
	CN	Owen et al., <i>Metal-Chalcogenide Photoresists for High Resolution Lithography and Sub-Micron Structures</i> , NANOSTRUCTURE PHYSICS AND FABRICATION, pp. 447-451 (M. Reed ed. 1989).		
	CO	Shimizu et al., <i>The Photo-Erasable Memory Switching Effect of Ag Photo-Doped Chalcogenide Glasses</i> , 46 B. CHEM SOC. JAPAN, No. 12, pp. 3662-3365 (1973).		
	CP	Abdel-All, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge <sub>5</sub> As <sub>38</sub> Te <sub>57</sub> chalcogenide glass, Vacuum 59 (2000) 845-853.		
	CQ	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.		
	CR	Adler, D.; Henisch, H.K.; Mott, S.N., The mechanism of threshold switching in amorphous alloys, Rev. Mod. Phys. 50 (1978) 209-220.		
	CS	Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se <sub>75</sub> Ge <sub>25</sub> -xSbx, Appl. Phys. A 55 (1992) 167-169.		
	CT	Afifi, M.A.; Labib, H.H.; Fouad, S.S.; El-Shazly, A.A., Electrical & thermal conductivity of the amorphous semiconductor GexSe1-x, Egypt, J. Phys. 17 (1986) 335-342.		
	CU	Aleksperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag <sub>2</sub> Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.		
	CV	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171.		
W	CW	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.		

Substitute for form 1449A/B/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)				<b>Complete if Known</b>	
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<i>W</i>	CX	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state Ionics 136-137 (2000) 1085-1089.	
	CY	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, J. Non-Cryst. Solids 11 (1972) 97-104.	
	CZ	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, Phys. Rev. Lett. 62 (1989) 808-810	
	CA1	Baranovskii, S.D.; Cordes, H., On the conduction mechanism in ionic glasses, J. Chem. Phys. 111 (1999) 7546-7557.	
	CB1	Belin, R.; Taillades, G.; Pradel, A.; Ribes, M., Ion dynamics in superionic chalcogenide glasses: complete conductivity spectra, Solid state Ionics 136-137 (2000) 1025-1029.	
	CC1	Belin, R.; Zerouale, A.; Pradel, A.; Ribes, M., Ion dynamics in the argyrodite compound Ag <sub>7</sub> GeSe <sub>5</sub> I: non-Arrhenius behavior and complete conductivity spectra, Solid State Ionics 143 (2001) 445-455.	
	CD1	Benmore, C.J.; Salmon, P.S., Structure of fast ion conducting and semiconducting glassy chalcogenide alloys, Phys. Rev. Lett. 73 (1994) 264-267.	
	CE1	Bernede, J.C., Influence du metal des electrodes sur les caracteristiques courant-tension des structures M-Ag <sub>2</sub> Se-M, Thin solid films 70 (1980) L1-L4.	
	CF1	Bernede, J.C., Polarized memory switching in MIS thin films, Thin Solid Films 81 (1981) 155-160.	
	CG1	Bernede, J.C., Switching and silver movements in Ag <sub>2</sub> Se thin films, Phys. Stat. Sol. (a) 57 (1980) K101-K104.	
	CH1	Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilayer electrode, Thin solid films 131 (1985) L61-L64.	
	CI1	Bernede, J.C.; Conan, A.; Fousenat, E.; El Bouchairi, B.; Goureaux, G., Polarized memory switching effects in Ag <sub>2</sub> Se/Se/M thin film sandwiches, Thin solid films 97 (1982) 165-171.	
	CJ1	Bernede, J.C.; Khelil, A.; Kettaf, M.; Conan, A., Transition from S- to N-type differential negative resistance in Al-Al <sub>2</sub> O <sub>3</sub> -Ag <sub>2</sub> -xSe <sub>1+x</sub> thin film structures, Phys. Stat. Sol. (a) 74 (1982) 217-224.	
	CK1	Bondarev, V.N.; Pikhitsa, P.V., A dendrite model of current instability in RbAg <sub>4</sub> 15, Solid State Ionics 70/71 (1994) 72-76.	
	CL1	Boolchand, P., The maximum in glass transition temperature (T <sub>g</sub> ) near x=1/3 in GexSe <sub>1-x</sub> Glasses, Aslan Journal of Physics (2000) 9, 709-72.	
	CM1	Boolchand, P.; Bresser, W.J., Mobile silver ions and glass formation in solid electrolytes, Nature 410 (2001) 1070-1073.	
	CN1	Boolchand, P.; Georgiev, D.G.; Goodman, B., Discovery of the Intermediate Phase in Chalcogenide Glasses, J. Optoelectronics and Advanced Materials, 3 (2001), 703	
	CO1	Boolchand, P.; Selvanathan, D.; Wang, Y.; Georgiev, D.G.; Bresser, W.J., Onset of rigidity in steps in chalcogenide glasses, Properties and Applications of Amorphous Materials, M.F. Thorpe and Tichy, L. (eds.) Kluwer Academic Publishers, the Netherlands, 2001, pp. 97-132.	
	CP1	Boolchand, P.; Enzweiler, R.N.; Tenhover, M., Structural ordering of evaporated amorphous chalcogenide alloy films: role of thermal annealing, Diffusion and Defect Data Vol. 53-54 (1987) 415-420.	
	CQ1	Boolchand, P.; Grothaus, J.; Bresser, W.J.; Suranyi, P., Structural origin of broken chemical order in a GeSe <sub>2</sub> glass, Phys. Rev. B 25 (1982) 2975-2978.	
	CR1	Boolchand, P.; Grothaus, J.; Phillips, J.C., Broken chemical order and phase separation in GexSe <sub>1-x</sub> glasses, Solid state comm. 45 (1983) 183-185.	
<i>W</i>	CS1	Boolchand, P., Bresser, W.J., Compositional trends in glass transition temperature (T <sub>g</sub> ), network connectivity and nanoscale chemical phase separation in chalcogenides, Dept. of ECECS, Univ. Cincinnati (October 28, 1999) 45221-0030.	

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21	CT1	Boolchand, P.; Grothaus, J, Molecular Structure of Melt-Quenched GeSe <sub>2</sub> and GeS <sub>2</sub> glasses compared, Proc. Int. Conf. Phys. Semicond. (Eds. Chadi and Harrison) 17 <sup>th</sup> (1985) 833-36.	
	CU1	Bresser, W.; Boolchand, P.; Suranyi, P., Rigidity percolation and molecular clustering in network glasses, Phys. Rev. Lett. 56 (1986) 2493-2496.	
	CV1	Bresser, W.J.; Boolchand, P.; Suranyi, P.; de Neufville, J.P, Intrinsically broken chalcogen chemical order in stoichiometric glasses, Journal de Physique 42 (1981) C4-193-C4-196.	
	CW1	Bresser, W.J.; Boolchand, P.; Suranyi, P.; Hernandez, J.G., Molecular phase separation and cluster size in GeSe <sub>2</sub> glass, Hyperfine Interactions 27 (1986) 389-392.	
	CX1	Cahen, D.; Gilet, J.-M.; Schmitz, C.; Chernyak, L.; Gartsman, K.; Jakubowicz, A., Room-Temperature, electric field induced creation of stable devices in CuInSe <sub>2</sub> Crystals, Science 258 (1992) 271-274.	
	CY1	Chatterjee, R.; Asokan, S.; Titus, S.S.K., Current-controlled negative-resistance behavior and memory switching in bulk As-Te-Se glasses, J. Phys. D: Appl. Phys. 27 (1994) 2624-2627.	
	CZ1	Chen, C.H.; Tai, K.L., Whisker growth induced by Ag photodoping in glassy GexSe1-x films, Appl. Phys. Lett. 37 (1980) 1075-1077.	
	CA2	Chen, G.; Cheng, J., Role of nitrogen in the crystallization of silicon nitride-doped chalcogenide glasses, J. Am. Ceram. Soc. 82 (1999) 2934-2936.	
	CB2	Chen, G.; Cheng, J.; Chen, W., Effect of Si <sub>3</sub> N <sub>4</sub> on chemical durability of chalcogenide glass, J. Non-Cryst. Solids 220 (1997) 249-253.	
	CC2	Cohen, M.H.; Neale, R.G.; Paskin, A., A model for an amorphous semiconductor memory device, J. Non-Cryst. Solids 8-10 (1972) 885-891.	
	CD2	Croitoru, N.; Lazarescu, M.; Popescu, C.; Telnic, M.; and Vescan, L., Ohmic and non-ohmic conduction in some amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 781-786.	
	CE2	Dalven, R.; Gill, R., Electrical properties of beta-Ag <sub>2</sub> Te and beta-Ag <sub>2</sub> Se from 4.2 to 300K, J. Appl. Phys. 38 (1967) 753-756.	
	CF2	Davis, E.A., Semiconductors without form, Search 1 (1970) 152-155.	
	CG2	Dearnaley, G.; Stoneham, A.M.; Morgan, D.V., Electrical phenomena in amorphous oxide films, Rep. Prog. Phys. 33 (1970) 1129-1191.	
	CH2	Dejus, R.J.; Susman, S.; Volin, K.J.; Montague, D.G.; Price, D.L., Structure of Vitreous Ag-Ge-Se, J. Non-Cryst. Solids 143 (1992) 162-180.	
	CI2	den Boer, W., Threshold switching in hydrogenated amorphous silicon, Appl. Phys. Lett. 40 (1982) 812-813.	
	CJ2	Drusedau, T.P.; Panckow, A.N.; Klabunde, F., The hydrogenated amorphous silicon/nanodisperse metal (SIMAL) system-Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832.	
	CK2	El Bouchairi, B.; Bernede, J.C.; Burgaud, P., Properties of Ag <sub>2</sub> -xSe <sub>1+x/n</sub> -Si diodes, Thin Solid Films 110 (1983) 107-113.	
	CL2	El Gharras, Z.; Bourahla, A.; Vautier, C., Role of photoinduced defects in amorphous GexSe1-x photoconductivity, J. Non-Cryst. Solids 155 (1993) 171-179.	
	CM2	El Ghrandi, R.; Calas, J.; Galibert, G.; Averous, M., Silver photodissolution in amorphous chalcogenide thin films, Thin Solid Films 218 (1992) 259-273.	
	CN2	El Ghrandi, R.; Calas, J.; Galibert, G., Ag dissolution kinetics in amorphous GeSe <sub>5.5</sub> thin films from "in-situ" resistance measurements vs time, Phys. Stat. Sol. (a) 123 (1991) 451-460.	
	CO2	El-kady, Y.L., The threshold switching in semiconducting glass Ge <sub>21</sub> Se <sub>17</sub> Te <sub>62</sub> , Indian J. Phys. 70A (1996) 507-516.	
	CP2	Elliott, S.R., A unified mechanism for metal photodissolution in amorphous chalcogenide materials, J. Non-Cryst. Solids 130 (1991) 85-97.	
21	CQ2	Elliott, S.R., Photodissolution of metals in chalcogenide glasses: A unified mechanism, J.	

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		Non-Cryst. Solids 137-138 (1991) 1031-1034.	
21/	CR2	Elsamanoudy, M.M.; Hegab, N.A.; Fadel, M., Conduction mechanism in the pre-switching state of thin films containing Te As Ge Si, Vacuum 46 (1995) 701-707.	
	CS2	El-Zahed, H.; El-Korashy, A., Influence of composition on the electrical and optical properties of Ge <sub>20</sub> BixSe <sub>80-x</sub> films, Thin Solid Films 376 (2000) 236-240.	
	CT2	Fadel, M., Switching phenomenon in evaporated Se-Ge-As thin films of amorphous chalcogenide glass, Vacuum 44 (1993) 851-855.	
	CU2	Fadel, M.; El-Shair, H.T., Electrical, thermal and optical properties of Se <sub>75</sub> Ge <sub>7</sub> Sb <sub>18</sub> , Vacuum 43 (1992) 253-257.	
	CV2	Feng, X.; Bresser, W.J.; Boolchand, P., Direct evidence for stiffness threshold in Chalcogenide glasses, Phys. Rev. Lett. 78 (1997) 4422-4425.	
	CW2	Feng, X.; Bresser, W.J.; Zhang, M.; Goodman, B.; Boolchand, P., Role of network connectivity on the elastic, plastic and thermal behavior of covalent glasses, J. Non-Cryst. Solids 222 (1997) 137-143.	
	CX2	Fischer-Colbrie, A.; Bienenstock, A.; Fuoss, P.H.; Marcus, M.A., Structure and bonding in photodiffused amorphous Ag-GeSe <sub>2</sub> thin films, Phys. Rev. B 38 (1988) 12388-12403.	
	CY2	Fleury, G.; Hamou, A.; Viger, C.; Vautier, C., Conductivity and crystallization of amorphous selenium, Phys. Stat. Sol. (a) 64 (1981) 311-316.	
	CZ2	Fritzsche, H., Optical and electrical energy gaps in amorphous semiconductors, J. Non-Cryst. Solids 6 (1971) 49-71.	
	CA3	Fritzsche, H., Electronic phenomena in amorphous semiconductors, Annual Review of Materials Science 2 (1972) 697-744.	
	CB3	Gates, B.; Wu, Y.; Yin, Y.; Yang, P.; Xia, Y., Single-crystalline nanowires of Ag <sub>2</sub> Se can be synthesized by templating against nanowires of trigonal Se, J. Am. Chem. Soc. (2001) currently ASAP.	
	CC3	Gosain, D.P.; Nakamura, M.; Shimizu, T.; Suzuki, M.; Okano, S., Nonvolatile memory based on reversible phase transition phenomena in telluride glasses, Jap. J. Appl. Phys. 28 (1989) 1013-1018.	
	CD3	Guin, J.-P.; Rouxel, T.; Keryvin, V.; Sangleboeuf, J.-C.; Serre, I.; Lucas, J., Indentation creep of Ge-Se chalcogenide glasses below T <sub>g</sub> : elastic recovery and non-Newtonian flow, J. Non-Cryst. Solids 298 (2002) 260-269.	
	CE3	Guin, J.-P.; Rouxel, T.; Sangleboeuf, J.-C.; Melscoet, I.; Lucas, J., Hardness, toughness, and scratchability of germanium-selenium chalcogenide glasses, J. Am. Ceram. Soc. 85 (2002) 1545-52.	
	CF3	Gupta, Y.P., On electrical switching and memory effects in amorphous chalcogenides, J. Non-Cryst. Sol. 3 (1970) 148-154.	
	CG3	Haberland, D.R.; Stiegler, H., New experiments on the charge-controlled switching effect in amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 408-414.	
	CH3	Haifz, M.M.; Ibrahim, M.M.; Dongol, M.; Hammad, F.H., Effect of composition on the structure and electrical properties of As-Se-Cu glasses, J. Appl. Phys. 54 (1983) 1950-1954.	
	CI3	Hajto, J.; Rose, M.J.; Osborne, I.S.; Snell, A.J.; Le Comber, P.G.; Owen, A.E., Quantization effects in metal/a-Si:H/metal devices, Int. J. Electronics 73 (1992) 911-913.	
	CJ3	Hajto, J.; Hu, J.; Snell, A.J.; Turvey, K.; Rose, M., DC and AC measurements on metal/a-Si:H/metal room temperature quantised resistance devices, J. Non-Cryst. Solids 266-269 (2000) 1058-1061.	
	CK3	Hajto, J.; McAuley, B.; Snell, A.J.; Owen, A.E., Theory of room temperature quantized resistance effects in metal-a-Si:H-metal thin film structures, J. Non-Cryst. Solids 198-200 (1996) 825-828.	
21/	CL3	Hajto, J.; Owen, A.E.; Snell, A.J.; Le Comber, P.G.; Rose, M.J., Analogue memory and	

Substitute for form 1449A/B/PTO			<b>Complete if Known</b>		
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)			Application Number	Not Yet Assigned	
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			Examiner Name	Not Yet Assigned	
Sheet	7	of	10	Attorney Docket Number	M4065.0635/P635 A

		ballistic electron effects in metal-amorphous silicon structures, Phil. Mag. B 63 (1991) 349-369.	
24	CM3	Hayashi, T.; Ono, Y.; Fukaya, M.; Kan, H., Polarized memory switching in amorphous Se film, Japan. J. Appl. Phys. 13 (1974) 1163-1164.	
	CN3	Hegab, N.A.; Fadel, M.; Sedeek, K., Memory switching phenomena in thin films of chalcogenide semiconductors, Vacuum 45 (1994) 459-462.	
	CO3	Hirose, Y.; Hirose, H., Polarity-dependent memory switching and behavior of Ag dendrite in Ag-photodoped amorphous As <sub>2</sub> S <sub>3</sub> films, J. Appl. Phys. 47 (1976) 2767-2772.	
	CP3	Hong, K.S.; Speyer, R.F., Switching behavior in II-IV-V <sub>2</sub> amorphous semiconductor systems, J. Non-Cryst. Solids 116 (1990) 191-200.	
	CQ3	Hosokawa, S., Atomic and electronic structures of glassy GexSe <sub>1-x</sub> around the stiffness threshold composition, J. Optoelectronics and Advanced Materials 3 (2001) 199-214.	
	CR3	Hu, J.; Snell, A.J.; Hajto, J.; Owen, A.E., Constant current forming in Cr/p+a-/Si:H/V thin film devices, J. Non-Cryst. Solids 227-230 (1998) 1187-1191.	
	CS3	Hu, J.; Hajto, J.; Snell, A.J.; Owen, A.E.; Rose, M.J., Capacitance anomaly near the metal-non-metal transition in Cr-hydrogenated amorphous Si-V thin-film devices, Phil. Mag. B. 74 (1996) 37-50.	
	CT3	Hu, J.; Snell, A.J.; Hajto, J.; Owen, A.E., Current-induced instability in Cr-p+a-Si:H-V thin film devices, Phil. Mag. B 80 (2000) 29-43.	
	CU3	Iizima, S.; Sugi, M.; Kikuchi, M.; Tanaka, K., Electrical and thermal properties of semiconducting glasses As-Te-Ge, Solid State Comm. 8 (1970) 153-155.	
	CV3	Ishikawa, R.; Kikuchi, M., Photovoltaic study on the photo-enhanced diffusion of Ag in amorphous films of Ge <sub>2</sub> S <sub>3</sub> , J. Non-Cryst. Solids 35 & 36 (1980) 1061-1066.	
	CW3	Iyetomi, H.; Vashishta, P.; Kalia, R.K., Incipient phase separation in Ag/Ge/Se glasses: clustering of Ag atoms, J. Non-Cryst. Solids 262 (2000) 135-142.	
	CX3	Jones, G.; Collins, R.A., Switching properties of thin selenium films under pulsed bias, Thin Solid Films 40 (1977) L15-L18.	
	CY3	Joullie, A.M.; Marucchi, J., On the DC electrical conduction of amorphous As <sub>2</sub> Se <sub>7</sub> before switching, Phys. Stat. Sol. (a) 13 (1972) K105-K109.	
	CZ3	Joullie, A.M.; Marucchi, J., Electrical properties of the amorphous alloy As <sub>2</sub> Se <sub>5</sub> , Mat. Res. Bull. 8 (1973) 433-442.	
	CA4	Kaplan, T.; Adler, D., Electrothermal switching in amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 538-543.	
	CB4	Kawaguchi, T.; Maruno, S.; Elliott, S.R., Optical, electrical, and structural properties of amorphous Ag-Ge-S and Ag-Ge-Se films and comparison of photoinduced and thermally induced phenomena of both systems, J. Appl. Phys. 79 (1996) 9096-9104.	
	CC4	Kawaguchi, T.; Masui, K., Analysis of change in optical transmission spectra resulting from Ag photodoping in chalcogenide film, Japn. J. Appl. Phys. 26 (1987) 15-21.	
	CD4	Kawasaki, M.; Kawamura, J.; Nakamura, Y.; Aniya, M., Ionic conductivity of Ag <sub>x</sub> (GeSe <sub>3</sub> ) <sub>1-x</sub> (0<x<0.571) glasses, Solid state Ionics 123 (1999) 259-269.	
	CE4	Kluge, G.; Thomas, A.; Klages, R.; Grotzschel, R., Silver photodiffusion in amorphous GexSe <sub>100-x</sub> , J. Non-Cryst. Solids 124 (1990) 186-193.	
	CF4	Kolobov, A.V., On the origin of p-type conductivity in amorphous chalcogenides, J. Non-Cryst. Solids 198-200 (1996) 728-731.	
	CG4	Kolobov, A.V., Lateral diffusion of silver in vitreous chalcogenide films, J. Non-Cryst. Solids 137-138 (1991) 1027-1030.	
24	CH4	Korkinova, Ts.N.; Andreichin, R.E., Chalcogenide glass polarization and the type of contacts, J. Non-Cryst. Solids 194 (1996) 256-259.	

Substitute for form 1449A/B/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)				<b>Complete if Known</b>	
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				Examiner Name	Not Yet Assigned
Sheet	8	of	10	Attorney Docket Number	M4065.0635/P635 A

38	CI4	Kotkata, M.F.; Afif, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTe chalcogenide semiconductor films, Thin Solid Films 240 (1994) 143-146.	
	CJ4	Lakshminarayan, K.N.; Srivastava, K.K.; Panwar, O.S.; Dumar, A., Amorphous semiconductor devices: memory and switching mechanism, J. Instn Electronics & Telecom. Engrs 27 (1981) 16-19.	
	CK4	Lal, M.; Goyal, N., Chemical bond approach to study the memory and threshold switching chalcogenide glasses, Indian Journal of pure & appl. phys. 29 (1991) 303-304.	
	CL4	Leimer, F.; Stotzel, H.; Kottwitz, A., Isothermal electrical polarisation of amorphous GeSe films with blocking Al contacts influenced by Poole-Frenkel conduction, Phys. Stat. Sol. (a) 29 (1975) K129-K132.	
	CM4	Leung, W.; Cheung, N.; Neureuther, A.R., Photoinduced diffusion of Ag in GexSe1-x glass, Appl. Phys. Lett. 46 (1985) 543-545.	
	CN4	Matsushita, T.; Yamagami, T.; Okuda, M., Polarized memory effect observed on Se-SnO2 system, Jap. J. Appl. Phys. 11 (1972) 1657-1662.	
	CO4	Matsushita, T.; Yamagami, T.; Okuda, M., Polarized memory effect observed on amorphous selenium thin films, Jpn. J. Appl. Phys. 11 (1972) 606.	
	CP4	Mazurier, F.; Levy, M.; Souquet, J.L, Reversible and irreversible electrical switching in TeO2-V2O5 based glasses, Journal de Physique IV 2 (1992) C2-185 - C2-188.	
	CQ4	Messoussi, R.; Bernede, J.C.; Benhida, S.; Abachi, T.; Latef, A., Electrical characterization of M/Se structures (M=Ni,Bi), Mat. Chem. And Phys. 28 (1991) 253-258.	
	CR4	Mitkova, M.; Boolchand, P., Microscopic origin of the glass forming tendency in chalcogenides and constraint theory, J. Non-Cryst. Solids 240 (1998) 1-21.	
	CS4	Mitkova, M.; Kozicki, M.N., Silver incorporation in Ge-Se glasses used in programmable metallization cell devices, J. Non-Cryst. Solids 299-302 (2002) 1023-1027.	
	CT4	Mitkova, M.; Wang, Y.; Boolchand, P., Dual chemical role of Ag as an additive in chalcogenide glasses, Phys. Rev. Lett. 83 (1999) 3848-3851.	
	CU4	Miyatani, S.-y., Electronic and ionic conduction in (AgxCu1-x)2Se, J. Phys. Soc. Japan 34 (1973) 423-432.	
	CV4	Miyatani, S.-y., Electrical properties of Ag2Se, J. Phys. Soc. Japan 13 (1958) 317.	
	CW4	Miyatani, S.-y., Ionic conduction in beta-Ag2Te and beta-Ag2Se, Journal Phys. Soc. Japan 14 (1959) 996-1002.	
	CX4	Mott, N.F., Conduction in glasses containing transition metal ions, J. Non-Cryst. Solids 1 (1968) 1-17.	
	CY4	Nakayama, K.; Kitagawa, T.; Ohmura, M.; Suzuki, M., Nonvolatile memory based on phase transitions in chalcogenide thin films, Jpn. J. Appl. Phys. 32 (1993) 564-569.	
	CZ4	Nakayama, K.; Kojima, K.; Hayakawa, F.; Imai, Y.; Kitagawa, A.; Suzuki, M., Submicron nonvolatile memory cell based on reversible phase transition in chalcogenide glasses, Jpn. J. Appl. Phys. 39 (2000) 6157-6161.	
	CA5	Nang, T.T.; Okuda, M.; Matsushita, T.; Yokota, S.; Suzuki, A., Electrical and optical parameters of GexSe1-x amorphous thin films, Jap. J. App. Phys. 15 (1976) 849-853.	
	CB5	Narayanan, R.A.; Asokan, S.; Kumar, A., Evidence concerning the effect of topology on electrical switching in chalcogenide network glasses, Phys. Rev. B 54 (1996) 4413-4415.	
	CC5	Neale, R.G.; Aseltine, J.A., The application of amorphous materials to computer memories, IEEE transactions on electron dev. Ed-20 (1973) 195-209.	
	CD5	Ovshinsky S.R.; Fritzsche, H., Reversible structural transformations in amorphous semiconductors for memory and logic, Metallurgical transactions 2 (1971) 641-645.	
40	CE5	Ovshinsky, S.R., Reversible electrical switching phenomena in disordered structures, Phys. Rev. Lett. 21 (1968) 1450-1453.	



Substitute for form 1449A/B/PTO				<b>Complete if Known</b>	
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(Use as many sheets as necessary)				Attorney Docket Number	M4065.0635/P635 A
Sheet	9	of	10		

24	CF5	Owen, A.E.; LeComber, P.G.; Sarabayrouse, G.; Spear, W.E., New amorphous-silicon electrically programmable nonvolatile switching device, IEE Proc. 129 (1982) 51-54	
	CG5	Owen, A.E.; Firth, A.P.; Ewen, P.J.S., Photo-induced structural and physico-chemical changes in amorphous chalcogenide semiconductors, Phil. Mag. B 52 (1985) 347-362.	
	CH5	Owen, A.E.; LeComber, P.G.; Hajto, J.; Rose, M.J.; Snell, A.J., Switching in amorphous devices, Int. J. Electronics 73 (1992) 897-906.	
	CI5	Pearson, A.D.; Miller, C.E., Filamentary conduction in semiconducting glass diodes, App. Phys. Lett. 14 (1969) 280-282.	
	CJ5	Pinto, R.; Ramanathan, K.V., Electric field induced memory switching in thin films of the chalcogenide system Ge-As-Se, Appl. Phys. Lett. 19 (1971) 221-223.	
	CK5	Popescu, C., The effect of local non-uniformities on thermal switching and high field behavior of structures with chalcogenide glasses, Solid-state electronics 18 (1975) 671-681.	
	CL5	Popescu, C.; Croitoru, N., The contribution of the lateral thermal instability to the switching phenomenon, J. Non-Cryst. Solids 8-10 (1972) 531-537.	
	CM5	Popov, A.I.; Geller, I.KH.; Shemetova, V.K., Memory and threshold switching effects in amorphous selenium, Phys. Stat. Sol. (a) 44 (1977) K71-K73.	
	CN5	Prakash, S.; Asokan, S.; Ghare, D.B., Easily reversible memory switching in Ge-As-Te glasses, J. Phys. D: Appl. Phys. 29 (1996) 2004-2008.	
	CO5	Rahman, S.; Sivarama Sastry, G., Electronic switching in Ge-Bi-Se-Te glasses, Mat. Sci. and Eng. B12 (1992) 219-222.	
	CP5	Ramesh, K.; Asokan, S.; Sangunni, K.S.; Gopal, E.S.R., Electrical Switching in germanium telluride glasses doped with Cu and Ag, Appl. Phys. A 69 (1999) 421-425.	
	CQ5	Rose, M.J.; Hajto, J.; Lecomber, P.G.; Gage, S.M.; Choi, W.K.; Snell, A.J.; Owen, A.E., Amorphous silicon analogue memory devices, J. Non-Cryst. Solids 115 (1989) 168-170.	
	CR5	Rose, M.J.; Snell, A.J.; Lecomber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in a -Si:H memory devices, Mat. Res. Soc. Symp. Proc. V 258, 1992, 1075-1080.	
	CS5	Schucker, D.; Rieder, G., On the reliability of amorphous chalcogenide switching devices, J. Non-Cryst. Solids 29 (1978) 397-407.	
	CT5	Sharma, A.K.; Singh, B., Electrical conductivity measurements of evaporated selenium films in vacuum, Proc. Indian Natn. Sci. Acad. 46, A, (1980) 362-368.	
	CU5	Sharma, P., Structural, electrical and optical properties of silver selenide films, Ind. J. Of pure and applied phys. 35 (1997) 424-427.	
	CV5	Snell, A.J.; Lecomber, P.G.; Hajto, J.; Rose, M.J.; Owen, A.E.; Osborne, I.L., Analogue memory effects in metal/a-Si:H/metal memory devices, J. Non-Cryst. Solids 137-138 (1991) 1257-1262.	
	CW5	Snell, A.J.; Hajto, J.; Rose, M.J.; Osborne, L.S.; Holmes, A.; Owen, A.E.; Gibson, R.A.G., Analogue memory effects in metal/a-Si:H/metal thin film structures, Mat. Res. Soc. Symp. Proc. V 297, 1993, 1017-1021.	
	CX5	Stevenson, A.G., Microfilaments in amorphous chalcogenide memory devices, J. Phys. D: Appl. Phys. 8 (1975) L120-L122.	
	CY5	Stevenson, A.G., The switching mechanisms in amorphous chalcogenide memory devices, J. Non-Cryst. Solids 21 (1976) 319-329.	
	CZ5	Stocker, H.J., Bulk and thin film switching and memory effects in semiconducting chalcogenide glasses, App. Phys. Lett. 15 (1969) 55-57.	
	CA6	Tanaka, K., Ionic and mixed conduction in Ag photodoping process, Mod. Phys. Lett B 4 (1990) 1373-1377.	
24	CB6	Tanaka, K.; Izima, S.; Sugli, M.; Okada, Y.; Kikuchi, M., Thermal effects on switching phenomenon in chalcogenide amorphous semiconductors, Solid State Comm. 8 (1970) 387-389.	

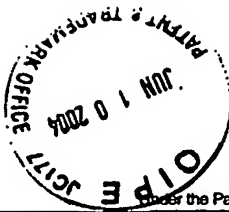
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Sheet	10	of	10	Attorney Docket Number	M4065.0635/P635 A

24	CC6	Thornburg, D.D., Memory switching in a Type I amorphous chalcogenide, J. Elect. Mat. 2 (1973) 3-15.	
	CD6	Thornburg, D.D., Memory switching in amorphous arsenic triselenide, J. Non-Cryst. Solids 11 (1972) 113-120.	
	CE6	Thornburg, D.D.; White, R.M., Electric field enhanced phase separation and memory switching in amorphous arsenic triselenide, Journal(??) (1972) 4609-4612.	
	CF6	Tichy, L.; Ticha, H., Remark on the glass-forming ability in GexSe1-x and AsxSe1-x systems, J. Non-Cryst. Solids 261 (2000) 277-281.	
	CG6	Titus, S.S.K.; Chatterjee, R.; Asokan, S., Electrical switching and short-range order in As-Te glasses, Phys. Rev. B 48 (1993) 14650-14652.	
	CH6	Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural investigation, Transport-structure relations in fast ion and mixed conductors Proceedings of the 6th Riso International symposium. 9-13 September 1985.	
	CI6	Tregouet, Y.; Bernede, J.C., Silver movements in Ag2Te thin films: switching and memory effects, Thin Solid Films 57 (1979) 49-54.	
	CJ6	Uemura, O.; Kameda, Y.; Kokai, S.; Satow, T., Thermally induced crystallization of amorphous Ge0.4Se0.6, J. Non-Cryst. Solids 117-118 (1990) 219-221.	
	CK6	Uttecht, R.; Stevenson, H.; Sie, C.H.; Griener, J.D.; Raghavan, K.S., Electric field induced filament formation in As-Te-Ge glass, J. Non-Cryst. Solids 2 (1970) 358-370.	
	CL6	Viger, C.; Lefrancois, G.; Fleury, G., Anomalous behaviour of amorphous selenium films, J. Non-Cryst. Solids 33 (1976) 267-272.	
	CM6	Vodenicharov, C.; Parvanov, S.; Petkov, P., Electrode-limited currents in the thin-film M-GeSe-M system, Mat. Chem. And Phys. 21 (1989) 447-454.	
	CN6	Wang, S.-J.; Misium, G.R.; Camp, J.C.; Chen, K.-L.; Tigelaar, H.L., High-performance Metal/silicide antifuse, IEEE electron dev. Lett. 13 (1992) 471-472.	
	CO6	Weirauch, D.F., Threshold switching and thermal filaments in amorphous semiconductors, App. Phys. Lett. 16 (1970) 72-73.	
	CP6	West, W.C.; Sieradzki, K.; Kardynal, B.; Kozicki, M.N., Equivalent circuit modeling of the Ag As0.24S0.36Ag0.40 Ag System prepared by photodissolution of Ag, J. Electrochem. Soc. 145 (1998) 2971-2974	
	CQ6	West, W.C., Electrically erasable non-volatile memory via electrochemical deposition of multifractal aggregates, Ph.D. Dissertation, ASU 1998	
	CR6	Zhang, M.; Mancini, S.; Bresser, W.; Boolchand, P., Variation of glass transition temperature, Tg, with average coordination number, <m>, in network glasses: evidence of a threshold behavior in the slope  dTg/d<m>  at the rigidity percolation threshold (<m>=2.4), J. Non-Cryst. Solids 151 (1992) 149-154.	
25	CS6	Kawamoto, Y.; Nishida, M., Ionic Conduction IN As2-Ag2S, GeS2-GeS-Ag2S and P2S5-Ag2-S Glasses, Journal of Non-Crystalline Solids 20 (1976) 393-404	

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U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
22	A	US 2004/0035401	2/2004	Ramachandran et al.	
	B	US 2003/0212724	11/2003	Ovshinsky et al.	
	C	US 2003/0048744	3/2003	Ovshinsky et al.	
	D	US 2003/0212725	11/2003	Ovshinsky et al.	
	E	US RE 37,259E	7/2001	Ovshinsky	
	F	US 3,271,591	9/1966	Ovshinsky	
	G	US 3,961,314	6/1976	Klose et al.	
	H	US 3,966,317	6/1976	Wacks et al.	
	I	US 3,983,542	11/1976	Ovshinsky	
	J	US 3,988,720	10/1976	Ovshinsky	
	K	US 4,177,474	12/1979	Ovshinsky	
	L	US 4,267,261	5/1981	Hallman et al.	
	M	US 4,597,162	7/1986	Johnson et al.	
	N	US 4,608,296	8/1986	Keem et al.	
	O	US 4,637,895	1/1987	Ovshinsky et al.	
	P	US 4,646,266	2/1987	Ovshinsky et al.	
	Q	US 4,664,939	5/1987	Ovshinsky	
	R	US 4,668,968	5/1987	Ovshinsky et al.	
	S	US 4,670,763	6/1987	Ovshinsky et al.	
	T	US 4,673,957	6/1987	Ovshinsky et al.	
	U	US 4,678,679	7/1987	Ovshinsky	
	V	US 4,696,758	9/1987	Ovshinsky et al.	
	W	US 4,698,234	10/1987	Ovshinsky et al.	
	X	US 4,710,899	12/1987	Young et al.	
	Y	US 4,728,406	3/1988	Banerjee et al.	
	Z	US 4,737,379	4/1988	Hudgens et al.	
	A1	US 4,766,471	8/1988	Ovshinsky et al.	
	B1	US 4,769,338	9/1988	Ovshinsky et al.	
	C1	US 4,775,425	10/1988	Guha et al.	
	D1	US 4,788,594	11/1988	Ovshinsky et al.	
	E1	US 4,809,044	2/1989	Pryor et al.	
	F1	US 4,818,717	4/1989	Johnson et al.	
	G1	US 4,843,443	6/1989	Ovshinsky et al.	
	H1	US 4,845,533	7/1989	Pryor et al.	
	I1	US 4,853,785	8/1989	Ovshinsky et al.	
	J1	US 4,891,330	1/1990	Guha et al.	
	K1	US 5,128,099	7/1992	Strand et al.	
	L1	US 5,159,661	10/1992	Ovshinsky et al.	
	M1	US 5,166,758	11/1992	Ovshinsky et al.	
	N1	US 5,177,567	1/1993	Klersy et al.	
	O1	US 5,296,716	3/1994	Ovshinsky et al.	
	P1	US 5,335,219	8/1994	Ovshinsky et al.	
	Q1	US 5,359,205	10/1994	Ovshinsky	
	R1	US 5,341,328	8/1994	Ovshinsky et al.	
	S1	US 5,406,509	4/1995	Ovshinsky et al.	

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✓	T1	US 5,414,271	5/1995	Ovshinsky et al.	
	U1	US 5,534,711	7/1996	Ovshinsky et al.	
	V1	US 5,534,712	7/1996	Ovshinsky et al.	
	W1	US 5,536,947	7/1996	Klersy et al.	
	X1	US 5,543,737	8/1996	Ovshinsky	
	Y1	US 5,591,501	1/1997	Ovshinsky et al.	
	Z1	US 5,596,522	1/1997	Ovshinsky et al.	
	A2	US 5,687,112	11/1997	Ovshinsky	
	B2	US 5,694,054	12/1997	Ovshinsky et al.	
	C2	US 5,714,768	2/1998	Ovshinsky et al.	
	D2	US 5,825,046	10/1998	Czubatyj et al.	
	E2	US 5,912,839	6/1999	Ovshinsky et al.	
	F2	US 5,933,365	8/1999	Klersy et al.	
	G2	US 6,011,757	1/2000	Ovshinsky	
	H2	US 6,087,674	7/2000	Ovshinsky et al.	
	I2	US 6,141,241	10/2000	Ovshinsky et al.	
	J2	US 6,339,544	1/2002	Chiang et al.	
	K2	US 6,404,665	6/2002	Lowery et al.	
	L2	US 6,429,064	8/2002	Wicker	
	M2	US 6,437,383	8/2002	Xu	
	N2	US 6,462,984	10/2002	Xu et al.	
	O2	US 6,480,438	11/2002	Park	
	P2	US 6,487,113	11/2002	Park et al.	
	Q2	US 6,501,111	12/2002	Lowery	
	R2	US 6,507,061	1/2003	Hudgens et al.	
	S2	US 6,511,862	1/2003	Hudgens et al.	
	T2	US 6,511,867	1/2003	Lowery et al.	
	U2	US 6,512,241	1/2003	Lai	
	V2	US 6,514,805	2/2003	Xu et al.	
	W2	US 6,531,373	3/2003	Gill et al.	
	X2	US 6,534,781	3/2003	Dennison	
	Y2	US 6,545,287	4/2003	Chiang	
	Z2	US 6,545,907	4/2003	Lowery et al.	
	A3	US 6,555,860	4/2003	Lowery et al.	
	B3	US 6,563,164	5/2003	Lowery et al.	
	C3	US 6,566,700	5/2003	Xu	
	D3	US 6,567,293	5/2003	Lowery et al.	
	E3	US 6,569,705	5/2003	Chiang et al.	
	F3	US 6,570,784	5/2003	Lowery	
	G3	US 6,576,921	6/2003	Lowery	
	H3	US 6,586,761	7/2003	Lowery	
	I3	US 6,589,714	7/2003	Maimon et al.	
	J3	US 6,590,807	7/2003	Lowery	
	K3	US 6,593,176	7/2003	Dennison	
	L3	US 6,597,009	7/2003	Wicker	
	M3	US 6,605,527	8/2003	Dennison et al.	
	N3	US 6,613,604	9/2003	Maimon et al.	
	O3	US 6,621,095	9/2003	Chiang et al.	
	P3	US 6,625,054	9/2003	Lowery et al.	
✓	Q3	US 6,642,102	11/2003	Xu	

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				Application Number	10/800,707
				Filing Date	March 16, 2004
				First Named Inventor	Kristy A. Campbell
				Art Unit	2811
				Examiner Name	Not Yet Assigned
Sheet	3	of	3	Attorney Docket Number	M4065.0635/P635

7x	R3	US 6,646,297	11/2003	Dennison	
	S3	US 6,649,928	11/2003	Dennison	
	T3	US 6,667,900	12/2003	Lowery et al.	
	U3	US 6,671,710	12/2003	Ovshinsky et al.	
	V3	US 6,673,700	1/2004	Dennison et al.	
	W3	US 6,674,115	1/2004	Hudgens et al.	
	X3	US 6,687,427	2/2004	Ramalingam et al.	
	Y3	US 6,690,026	2/2004	Peterson	
	Z3	US 6,696,355	2/2004	Dennison	
	A4	US 6,687,153	2/2004	Lowery	
	B4	US 6,707,712	3/2004	Lowery	
7x	C4	US 6,714,954	3/2004	Ovshinsky et al.	

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
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U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
24	AA	US-6,673,648	01/06/2004	Lowrey	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>3</sup>
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*K. Picerno*

*7/13/05*